Abstract

To provide an etching method employing a novel CVD system and an etching apparatus applicable to the method.

In the etching method, performed are an adsorption step of employing halogen radicals generated from a halogen through formation of a plasma thereof, and a precursor 24 formed from the halogen and a noble metal component generated through etching of a noble metal member 11 by the halogen radicals, wherein crystal nuclei of the precursor 24 are caused to be adsorbed on a substrate 3; and an etching step of anisotropically etching, in a thickness direction by the halogen radicals, a portion of the substrate 3 on which the crystal nuclei have been adsorbed.